

In the Specification:

Please insert the following Section before "Field of the Invention" in the enclosed specification:

REFERENCE TO RELATED APPLICATIONS

A1 This application is a continuation of U.S. Nonprovisional Application No. 09/342,335, filed June 6, 1999, entitled "Method for Selectively Etching Silicon and/or Metal Silicides."

In the Claims:

Please cancel claims 13 and 16-20 and amend the claims as follows:

5b
2. (Amended) A method comprising etching a metal silicide layer during fabrication of an integrated circuit in an environment having a concentration of O₂ greater than 25 % by volume so as to selectively etch the metal silicide layer with respect to an underlying poly-silicon layer.

Please add claims 21-27 as follows:

5b
21. A method of etching a metal silicide, comprising etching of the metal silicide with a plasma, wherein the plasma is prepared from a gas mixture comprising: chlorine, and greater than 25 % by volume oxygen.

22. The method of claim 21, further comprising, prior to said etching, a breakthrough etch.

23. The method of claim 22, wherein said breakthrough etch comprises etching with a plasma prepared from a gas comprising CF₄.

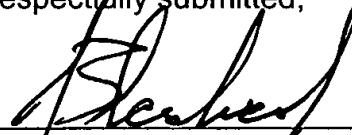
24. The method of claim 21, wherein said etching is a metal silicide etch that is selective to poly-silicon with a ratio of etch rates of at least 30.

Sub 1 25. The method of claim 1, further comprising, prior to said etching, a breakthrough etch.

26. The method of claim 1, wherein said etching is a metal silicide etch that is selective to poly-silicon with a ratio of etch rates of at least 30.

Sub 1 27. The method of claim 21, wherein said gas mixture comprises: chlorine and from 25 % to 30% by volume oxygen.

Respectfully submitted,



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